

产品概览

NTBG080N120SC1: Silicon Carbide MOSFET, N-Channel, 1200 V, 80 mΩ , D2PAK-7L

欲看完整文档，请参阅数据表。

Silicon Carbide (SiC) MOSFET uses a completely new technology that provide superior switching performance and higher reliability compared to Silicon. In addition, the low ON resistance and compact chip size ensure low capacitance and gate charge. Consequently, system benefits include highest efficiency, faster operation frequency, increased power density, reduced EMI, and reduced system size.

特性

- Low On Resistance
- High Junction Temperature
- Ultra Low Gate Charge
- Low Effective Output Capacitance
- This device is RoHS Compliant

优势

- $R_{DS(on)} = 80\text{m}\Omega$ typ
- $T_j = 175\text{C}$

应用

- DC-DC Converter
- Boost Inverter
- UPS

终端产品

- Solar
- Charging Station
- Motor Drive

器件电气规格

产品	Pricing (\$/Unit)	Compliance	Status	Channel Polarity	Configuration	Blocking Voltage V_{DSS} (V)	$I_{D(max)}$ (A)	$R_{DS(on)}$ Typ @ 25°C (mΩ)	Q_g Total (C)	Output Capacitance (C)	T_j Max (°C)	Package Type
NTBG080N120SC1	5.9999	Pb-free Halide free non AEC-Q and PPAP	NEW	N-Channel	Single	1200	30	80	56	79	175	D2PAK7 (TO-263-7L HV)

欲了解更多信息，请联系您当地的销售支援 www.onsemi.cn。

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